

ABSTRACT OF THE DISCLOSURE

Disclosed is a polymer for use in a chemically amplified resist, a resist composition including such a polymer is suitable for use in a chemically amplified resist, which is sensitive to far ultraviolet rays such as KrF or ArF excimer laser and forms a photoresist pattern having low dependence on and good adhesion to substrate, high transparency in the wavelength range of the above radiation, strong resistance to dry etching, and excellencies in sensitivity, resolution and developability. The resist composition can have a stronger etching resistance with a maximized content of unsaturated aliphatic ring in the polymer and a reduced edge roughness of the photoresist pattern with an alkoxyalkyl acrylate monomer employed.

100 200 300 400 500 600 700 800 900 1000

b
a